CPH3462

Power MOSFET 100V, 785mΩ, 1A, Single N-Channel



Features

• On-resistance $R_{DS}(on)1=590m\Omega$ (typ)

• Halogen free compliance

• 4V drive

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		100	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		1	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	4	А
Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

* Machine Model

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² ×0.8mm)	$R_{\theta J A}$	125	°C/W

Electrical Characteristics at Ta = 25°C

Deremeter				Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =0.5A		2.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	ID=1A, VGS=10V		590	785	mΩ
	R _{DS} (on)2	I _D =0.5A, V _{GS} =4V		650	930	mΩ
Input Capacitance	Ciss			155		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		11.9		pF
Reverse Transfer Capacitance	Crss]		5.8		pF

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

Continued from preceding page.						-
Parameter	Symbol	Conditions		Value		
	Symbol		min	Тур	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		4.0		ns
Rise Time	tr			2.8		ns
Turn-OFF Delay Time	t _d (off)			17		ns
Fall Time	tf			11		ns
Total Gate Charge	Qg	V _{DS} =50V, V _{GS} =10V, I _D =1A		3.4		nC
Gate to Source Charge	Qgs			0.47		nC
Gate to Drain "Miller" Charge	Qgd			0.72		nC
Forward Diode Voltage	VSD	IS=1A, VGS=0V		0.82	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

Device	Package	Shipping	note
CPH3462-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

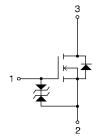
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Marking

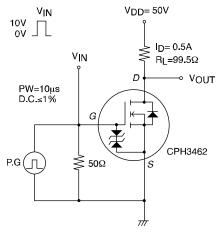


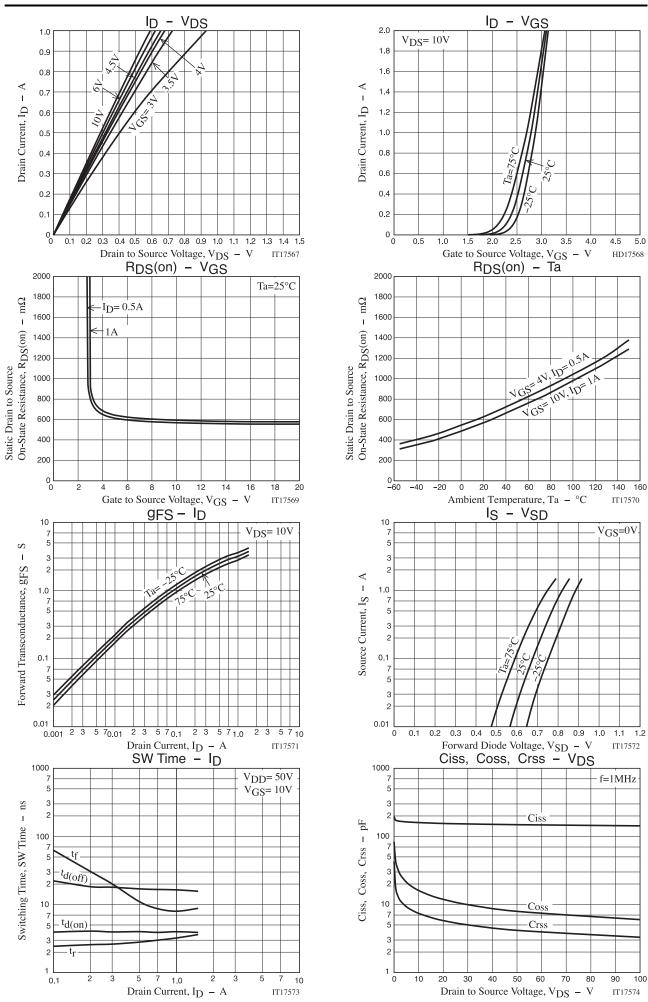


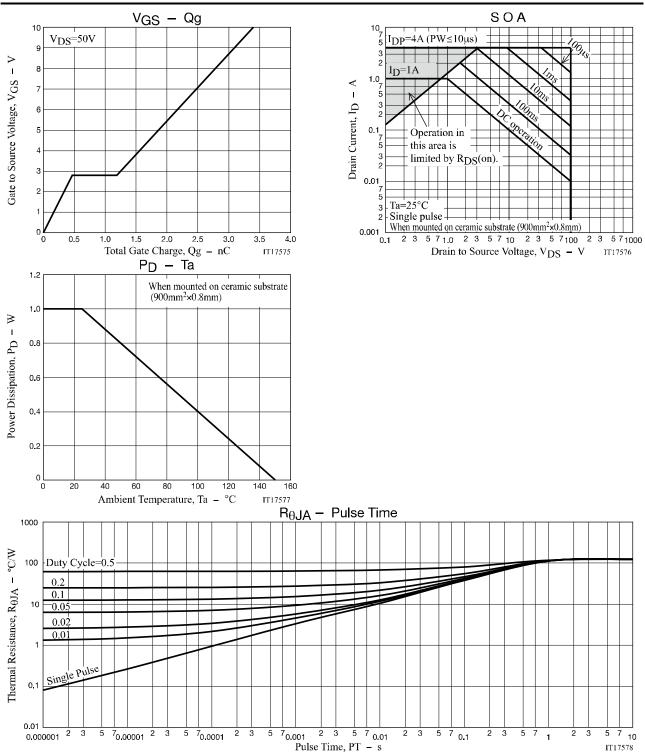
Electrical Connection



Switching Time Test Circuit



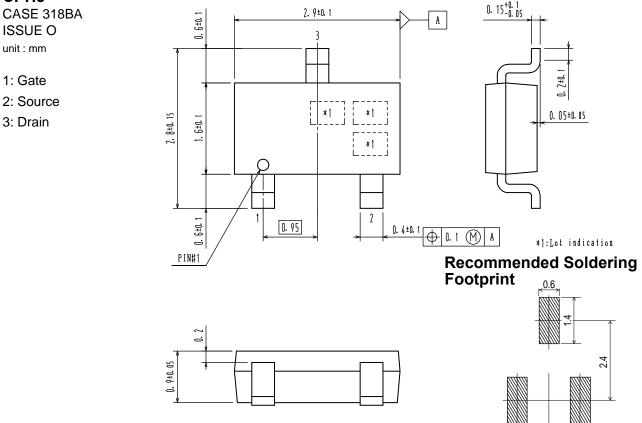




Package Dimensions

CPH3462-TL-W

CPH3



Note on usage : Since the CPH3462 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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